ESDBL6V8P

SILICON EPITAXIAL PLANAR DIODE

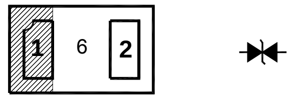
ESD protection diode

Features

- Ultra small mold type
- Bi-direction high reliability

PINNING

PIN	DESCRIPTION
1	Anode
2	Anode



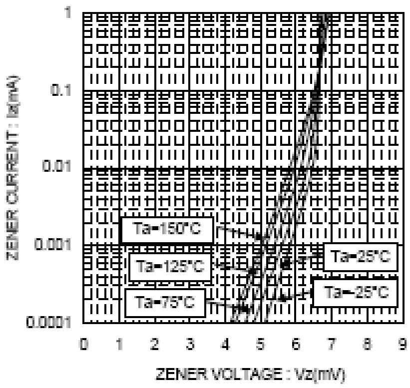
Transparent top view
Marking Code: 6
Simplified outline DFN1006-2H and symbol

Absolute Maximum Ratings (T_a = 25℃)

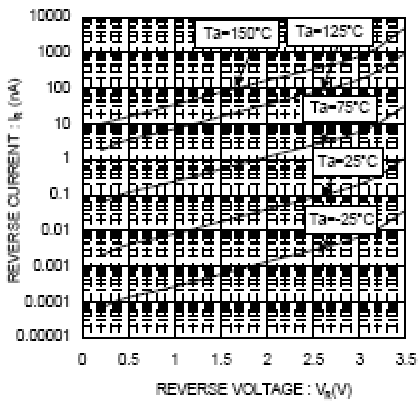
Parameter	Symbol	Value	Unit
Peak Pulse Power (tp = 10 X 1000 µs)	P_{PK}	10	W
Power Dissipation	P_D	100	mW
Junction Temperature	T_J	150	℃
Storage Temperature Range	T_{stg}	- 55 to + 150	℃
Operation Temperature Range	T_{opr}	- 55 to + 150	℃

Characteristics at T_a = 25℃

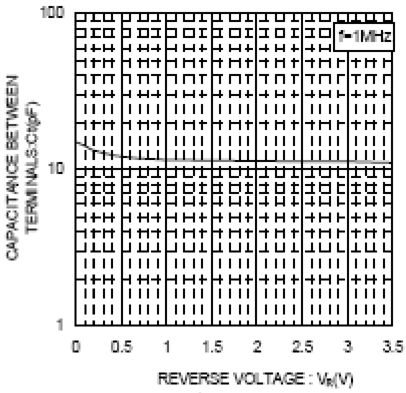
Parameter	Symbol	Min.	Typ.	Max.	Unit
Zener Voltage at I_Z = 1 mA	V_Z	5.78	-	7.82	V
Reverse Current at V_R = 3.5 V	I_R	-	-	0.5	µA
Capacitance between Terminals at V_R = 0 V, f = 1 MHz	C_T	-	15	-	pF



Vz-Iz CHARACTERISTICS



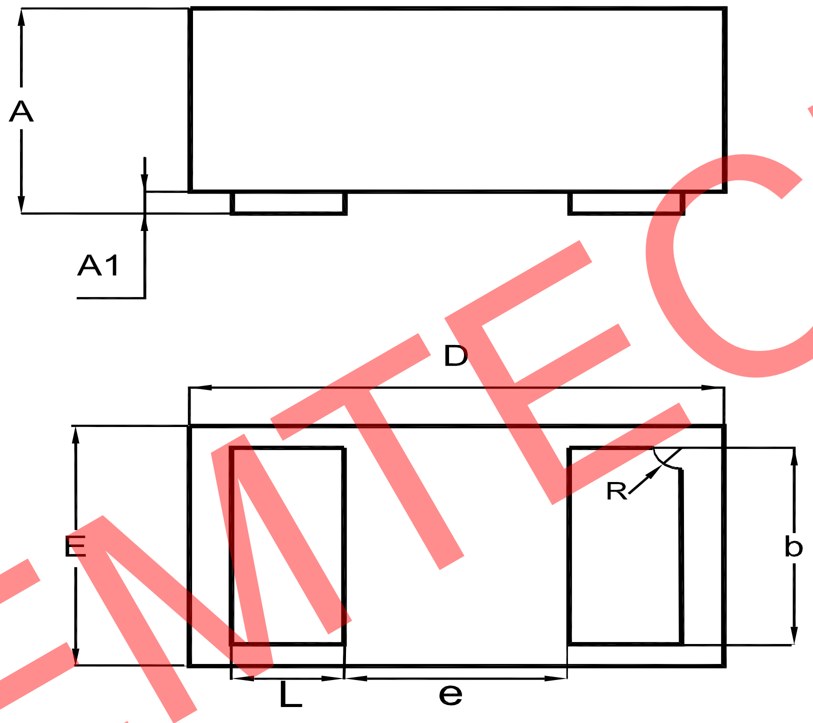
V_R-I_R CHARACTERISTICS



V_R-Ct CHARACTERISTICS

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads **DFN1006-2H**



UNIT	A	A1	b	D	E	e	L	R
mm	0.51	0.05	0.55	1.075	0.675	0.4	0.3	0.15
	0.46	0	0.45	0.95	0.55		0.2	0.05